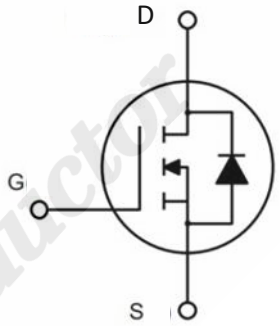
SiC MOS P3M171K0K3

N-Channel Enhancement Mode

Features

- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost

TO-247-3

Gate	1
Drain	2
Source	3

Applications

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies

RoHS

Halogen

Order Information

Part Number	Package	Marking
P3M171K0K3	TO-247-3	P3M171K0K3

Contents

1. Maximum Ratings

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	1700	V	V_{GS}= 0V I_D= 200μA
Gate - Source Voltage (Dynamic)	V_{GSmax}	-8 / +19	V	AC (f>1Hz)
Gate - Source Voltage (Static)	V_{GSop}	-3 / +15	V	Static
Continuous Drain Current	I_D	6	A	V_{GS}= 15V T_C= 25℃
		4		V_{GS}= 15V T_C= 100℃
Power Dissipation	P_D	68	W	
Operating Junction Temperature	T_J	-55 To +175	℃	
Storage Temperature	T_{stg}	-55 To +175	℃	
Solder Temperature	T_L	260	˚C	
Mounting Torque	M_d	1 8.8	Nm lbf-in	M3 or 6-32 screw

2. Electrical Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1700	/	/	V	V_{GS}= 0V I_D= 200μA
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.2	/	V	(tested after 30ms pulse at V_{GS}=15V) V_{DS}= V_{GS} I_D= 2mA T_J= 25°C
		/	1.45	/	V	V_{DS}= V_{GS} I_D= 2mA T_J= 175°C
Zero Gate Voltage Drain Current	I_{DSS}	/	2.6	200	μA	V_{GS}= 0V V_{DS}= 1700V
Gate-Source Leakage Current	I_{GSS}	/	2	125	nA	V_{GS}= 15V V_{DS}= 0V
Drain-Source On-State Resistance	$R_{DS(on)}$	/	1	1.4	Ω	V_{GS}= 15V I_D= 2A T_J= 25°C
		/	1.4	/		V_{GS}= 15V I_D= 2A T_J= 125°C
		/	1.7	/		V_{GS}= 15V I_D= 2A T_J= 175°C
Transconductance	g_{fs}	/	0.29	/	S	V_{DS}= 20V I_{DS}= 2A T_J= 25°C
		/	0.31	/		V_{DS}= 20V I_{DS}= 2A T_J= 175°C

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Input Capacitance	C_{iss}	/	235	/	pF	V_{GS}= 0V V_{DS}= 1000V f= 1MHz V_{AC}= 25mV
Output Capacitance	C_{oss}	/	8.9	/		
Reverse Transfer Capacitance	C_{rss}	/	2.8	/		
Coss Stored Energy	E_{oss}	/	9.4	/	μJ	
Turn-on Energy	E_{on}	/	95.7	/	μJ	V_{DS}= 1200V V_{GS}= -3/15V I_{DS}= 3A R_G= 1Ω
Turn-off Energy	E_{off}	/	16.9	/		
Turn-On Delay Time	$T_{d(on)}$	/	15.5	/	nS	
Rise Time	T_r	/	16.2	/		
Turn-Off Delay Time	$T_{d(off)}$	/	15.7	/		
Fall Time	T_f	/	31.2	/		
Internal Gate Resistance	$R_{G(int)}$	/	27	/	Ω	f=1MHz V_{AC}= 25mV
Gate to Source Charge	Q_{gs}	/	2.2	/	nC	V_{DS}= 1200V I_{DS}= 2A V_{GS}= -3 to 15V I_G= 2mA
Gate to Drain Charge	Q_{gd}	/	2.5	/		
Total Gate Charge	Q_g	/	7.4	/		

3. Reverse Diode Characteristics

At T_J=25 ℃, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.1	/	V	V_{GS}= -3V I_{SD}= 1A T_J= 25℃
		5.1	/	V	V_{GS}= -3V I_{SD}= 1A T_J= 175℃
Continuous Diode Forward Current	I_S	5	/	A	V_{GS}= -3V
Reverse Recover Time	t_{rr}	35.4	/	ns	V_{GS}= -3/15V I_{SD}= 3A V_R= 1200V d_{if}/d_t= 650A/μs T_J= 25℃
Reverse Recovery Charge	Q_{rr}	69.1	/	nC	
Peak Reverse Recovery Current	I_{rrm}	4.2	/	A	

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2.2	℃/W

5. Typical Performance

At T_J= 25℃, unless specified otherwise

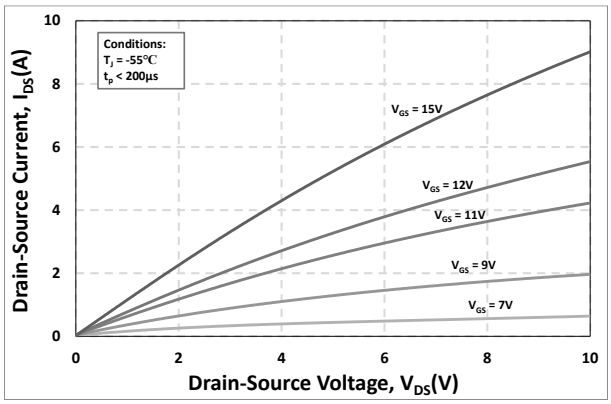


Figure 1. Output Characteristics T_J= -55℃

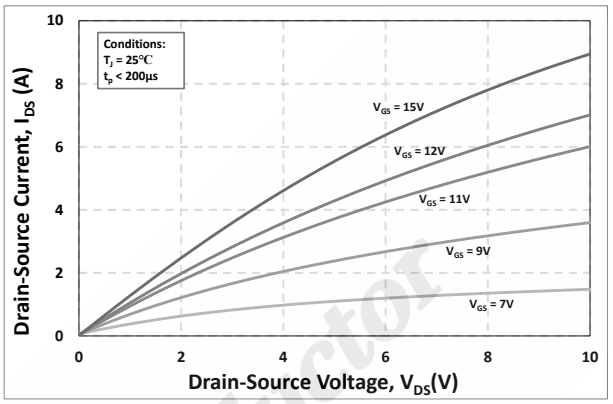


Figure 2. Output Characteristics T_J= 25℃

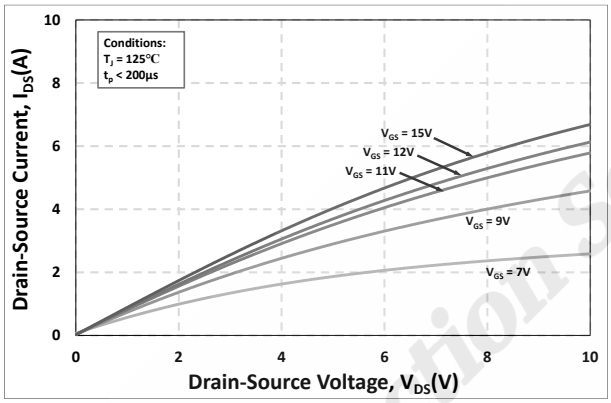


Figure 3. Output Characteristics T_J= 125℃

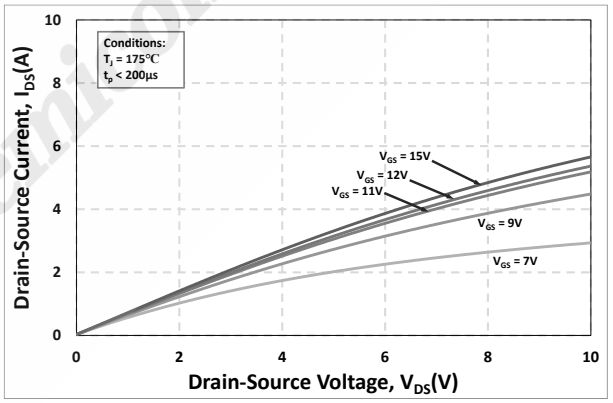


Figure 4. Output Characteristics T_J= 175℃

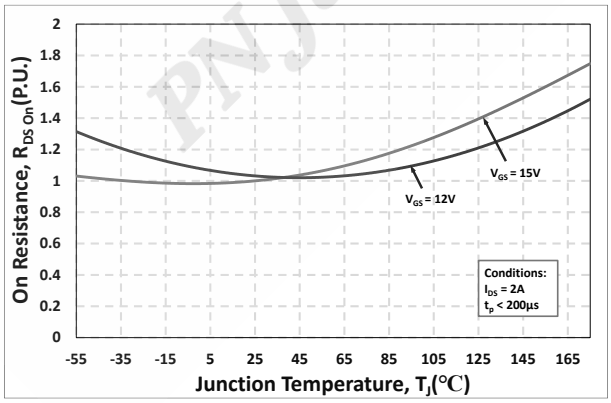


Figure 5. Normalized On-Resistance vs. Temperature

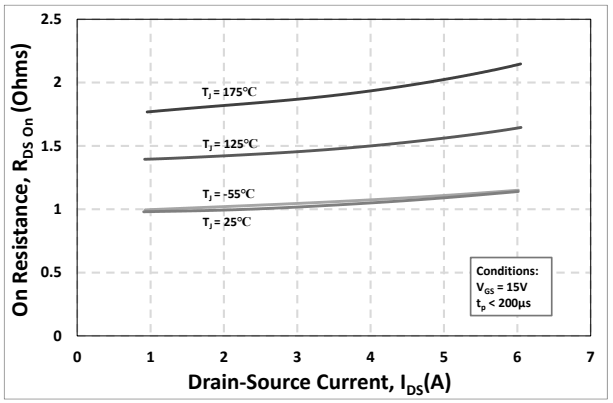


Figure 6. On-Resistance vs. Drain Current Various Temperatures

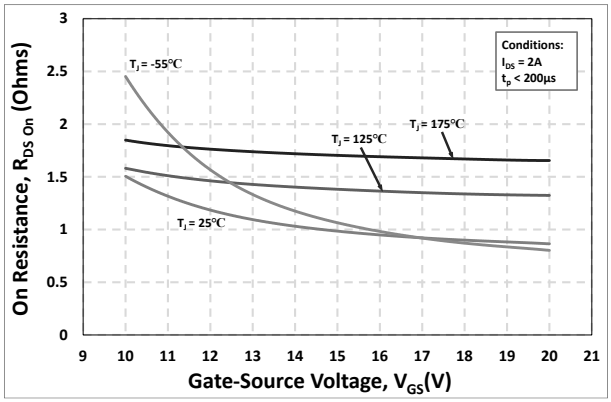


Figure 7. On-Resistance vs. Gate-Source Voltage

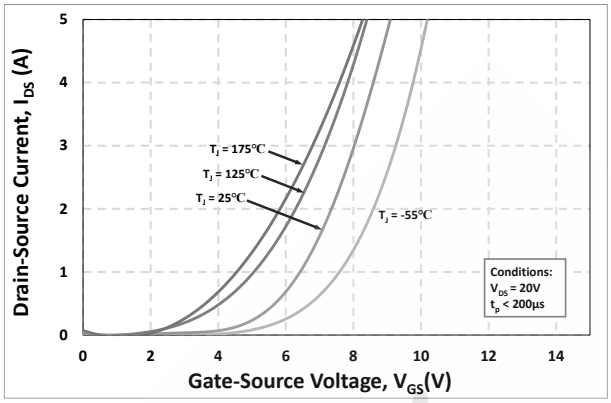


Figure 8. Transfer Characteristic for Various Junction Temperatures

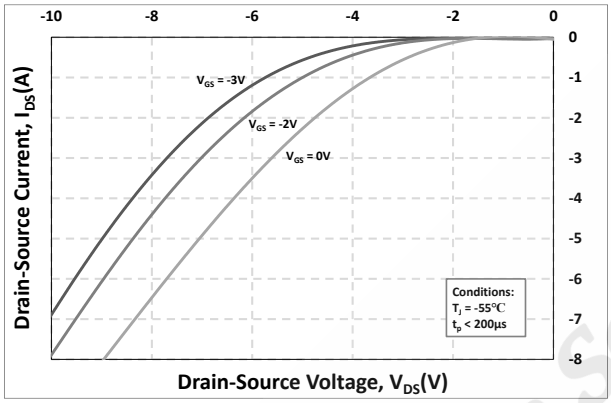


Figure 9. Body Diode Characteristic at -55°C

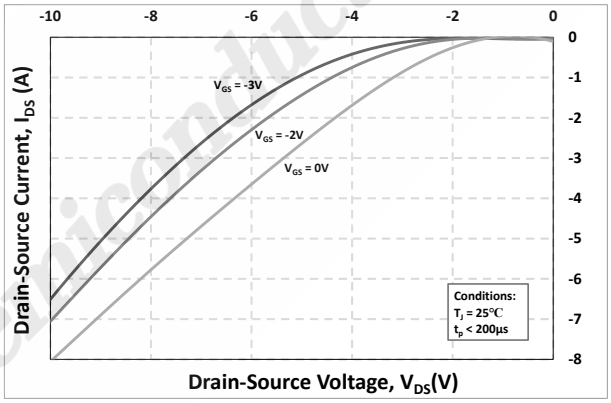


Figure 10. Body Diode Characteristic at 25°C

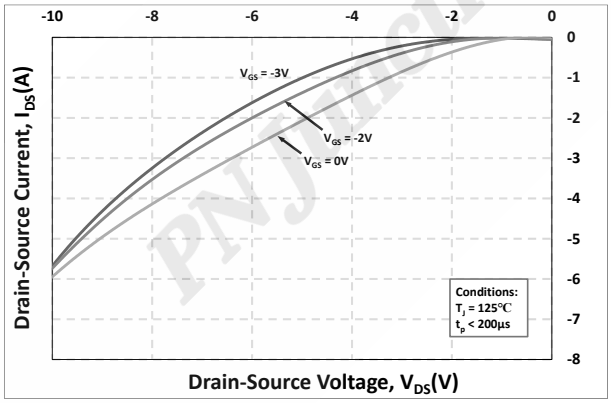


Figure 11. Body Diode Characteristic at 125°C

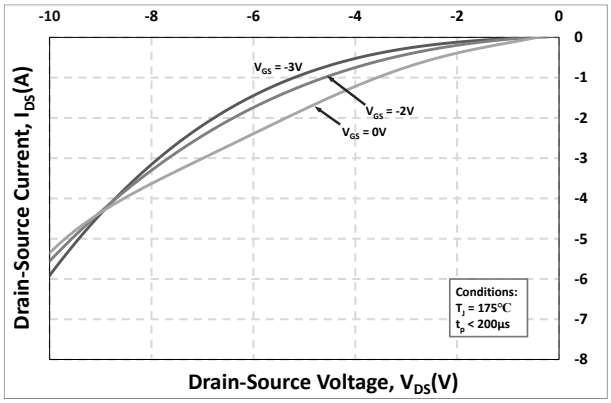


Figure 12. Body Diode Characteristic at 175°C

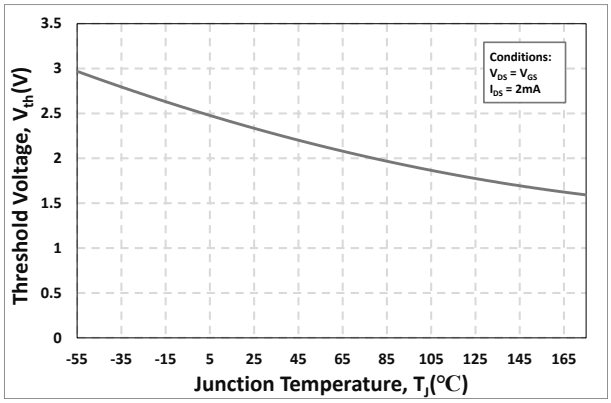


Figure 13. Threshold Voltage vs. Temperatures

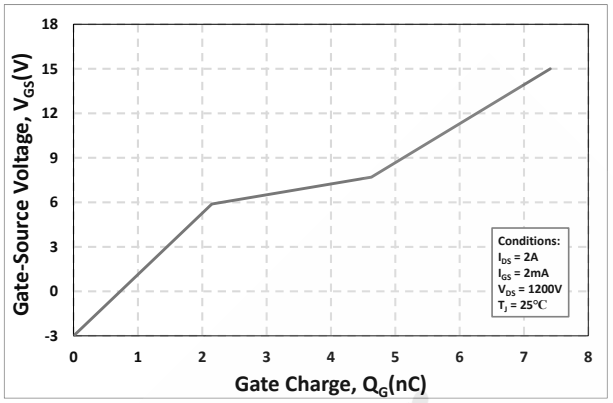


Figure 14. Gate Charge Characteristics

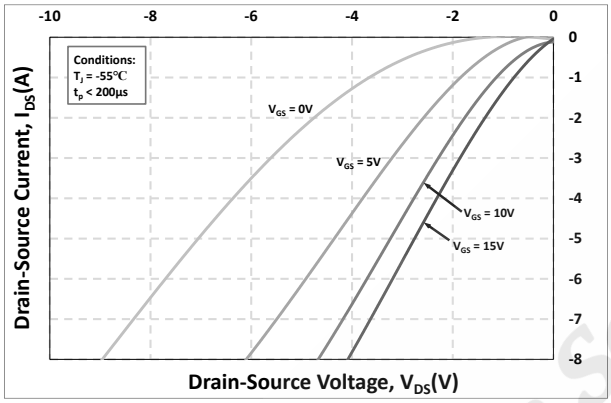


Figure 15. 3rd Quadrant Characteristic at -55℃

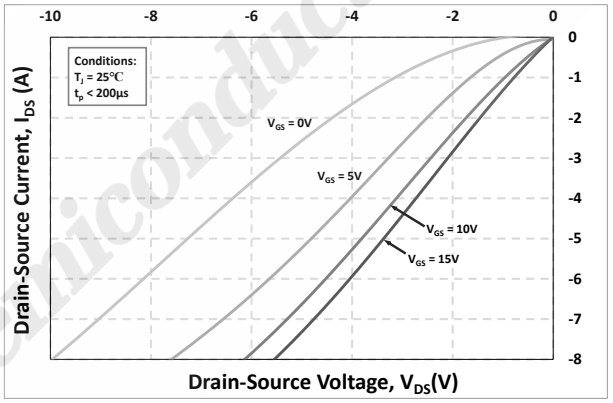


Figure 16. 3rd Quadrant Characteristic at 25℃

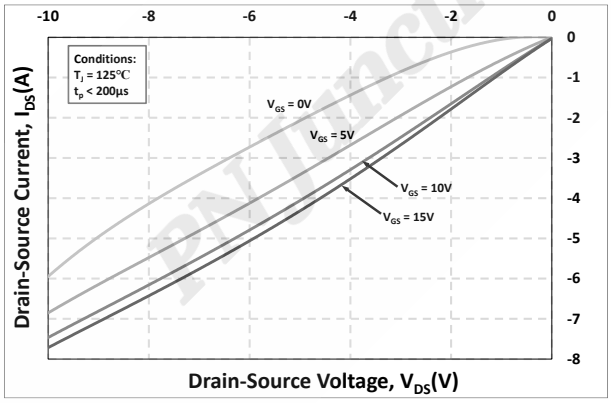


Figure 17. 3rd Quadrant Characteristic at 125 ℃

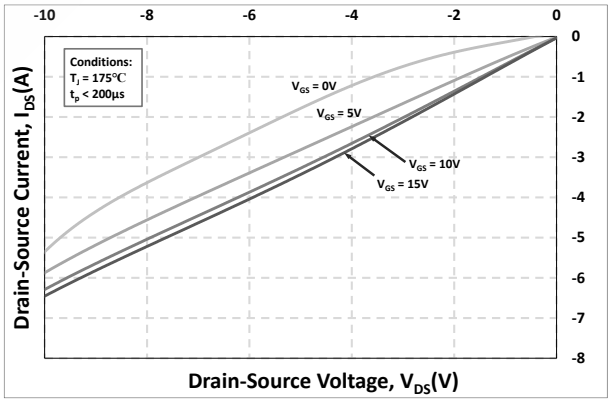


Figure 18. 3rd Quadrant Characteristic at 175 ℃

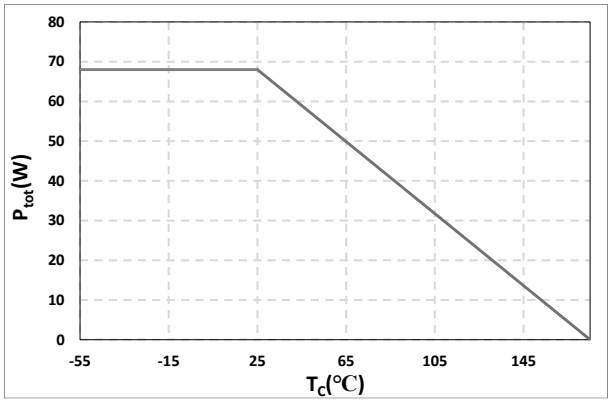


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

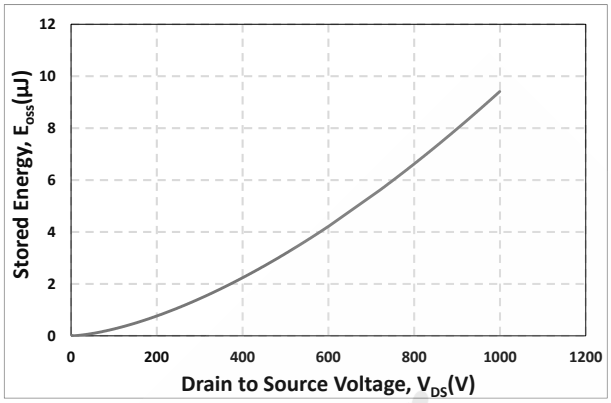


Figure 20. Output Capacitor Stored Energy

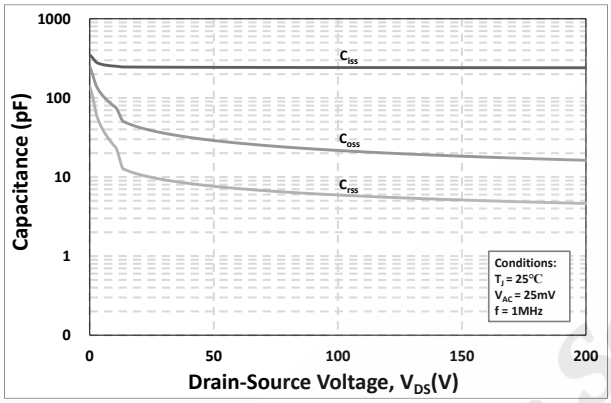


Figure 21. Capacitances vs. Drain-Source Voltage (0-200V)

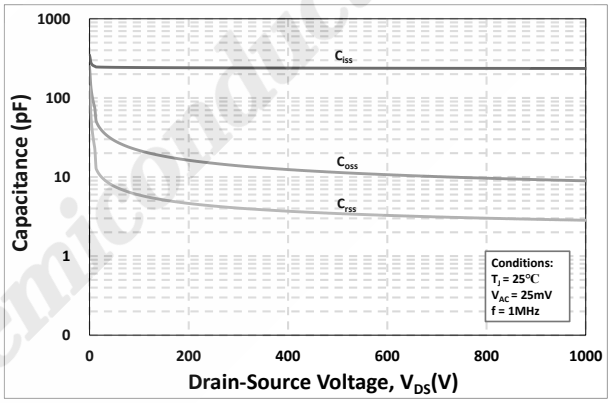


Figure 22. Capacitances vs. Drain-Source Voltage (0-1000V)

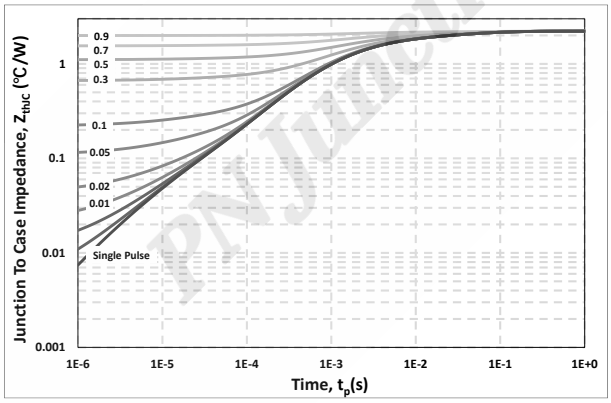


Figure 23. Transient Thermal Impedance (Junction - Case)

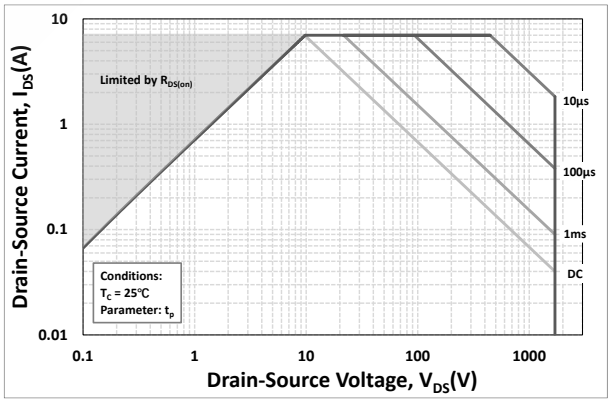


Figure 24. Safe Operating Area

6. Definitions

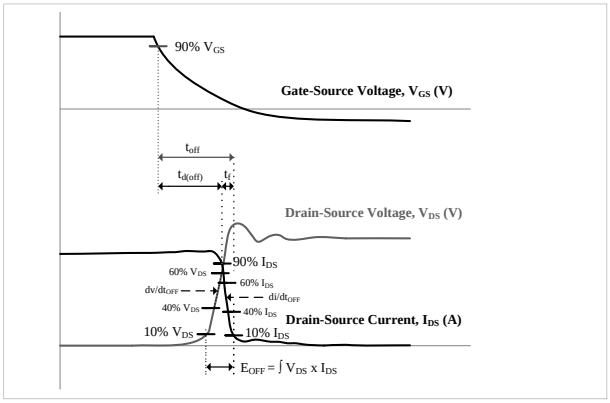


Figure 25. Turn-off Transient Definitions

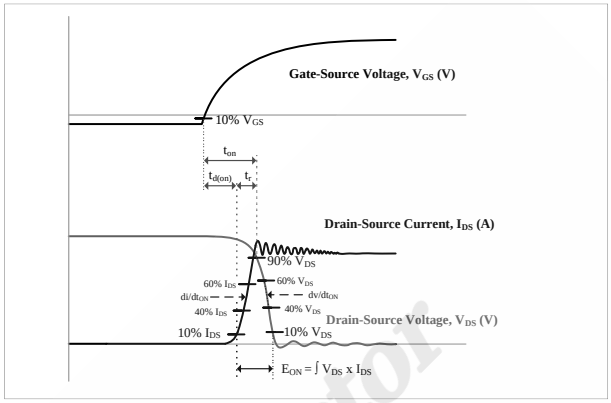


Figure 26. Turn-on Transient Definitions

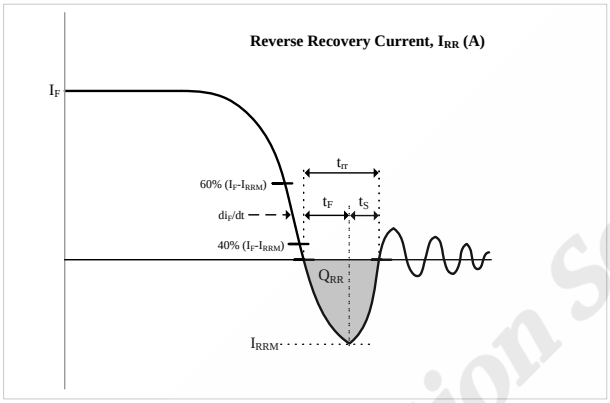


Figure 27. Reverse Recovery Definitions

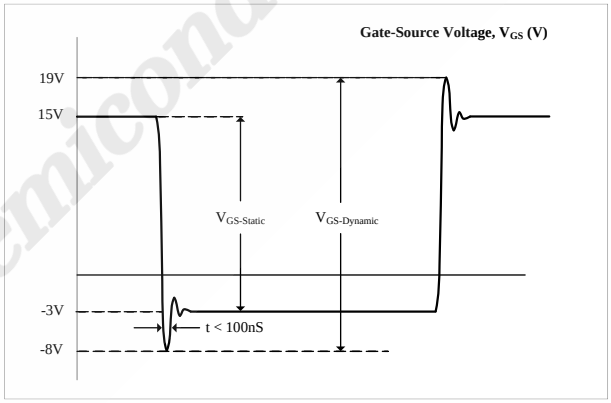
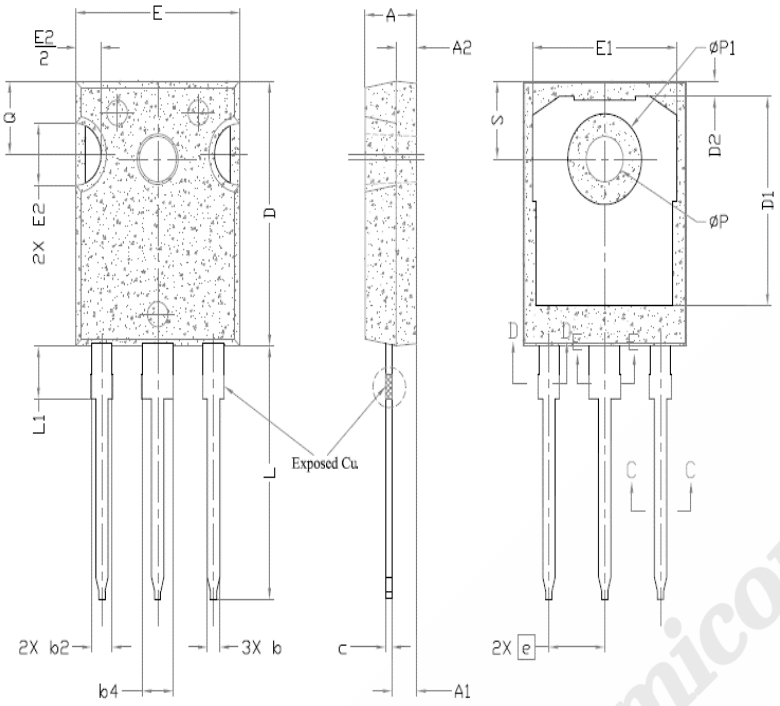


Figure 28. Vgs Transient Definitions

7. Package Outlines



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2,29	2,41	2,55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16,25	16,55	17,65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13,46	14,02	14,16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19,81	20,07	20,32	
L1	4,10	4,19	4,40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF.			
Q	5,39	5,79	6,20	
S	6.04	6.17	6.30	

Drawing and Dimensions

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